	No.1349C	GZB2.0 to 36
		Silicon Planar Type
1.0W Zener Diodes		

Features

- Glass sleeve structure
- Voltage regulator, surge absorber applications
- Power dissipation : $P = 1.0\text{mW}$
- Zener voltage : $V_Z = 2.0$ to 36V
- Small-sized package : JEDEC DO-41

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

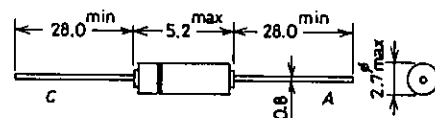
Power Dissipation	P	1	W
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +175	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Type No.	Zener Characteristics						Reverse Current		
	Zener Voltage, V_Z [V] ($t = 30\text{ms}$)				Dynamic Resistance r_d [Ω] $f = 1\text{kHz}$		Measured Current [mA]	I_R [μA]	Measured Voltage V_R [V]
	B		C		min	min			
	min	min	min	min					
GZB2.0	1.88	2.12	2.00	2.24	15	25	40	-200	-0.5
GZB2.2	2.08	2.33	2.20	2.45	12	20	40	-200	-0.7
GZB2.4	2.28	2.56	2.4	2.7	12	20	40	-200	-1
GZB2.7	2.5	2.9	2.7	3.1	9	15	40	-200	-1
GZB3.0	2.8	3.2	3.0	3.4	9	15	40	-100	-1
GZB3.3	3.1	3.5	3.3	3.7	9	15	40	-80	-1
GZB3.6	3.4	3.8	3.6	4.0	9	15	40	-60	-1
GZB3.9	3.7	4.1	3.9	4.4	9	15	40	-40	-1
GZB4.3	4.0	4.5	4.3	4.8	9	15	40	-20	-1
GZB4.7	4.4	4.9	4.7	5.2	7	10	40	-20	-1
GZB5.1	4.8	5.4	5.1	5.7	5	8	40	-20	-1
GZB5.6	5.3	6.0	5.6	6.3	5	8	40	-20	-1.5
GZB6.2	5.8	6.6	6.2	7.0	3	6	40	-20	-3
GZB6.8	6.4	7.2	6.8	7.7	3	6	40	-20	-3.5

Continued on next page.

Package Dimensions 1134 (unit: mm)



C: Cathode
A: Anode

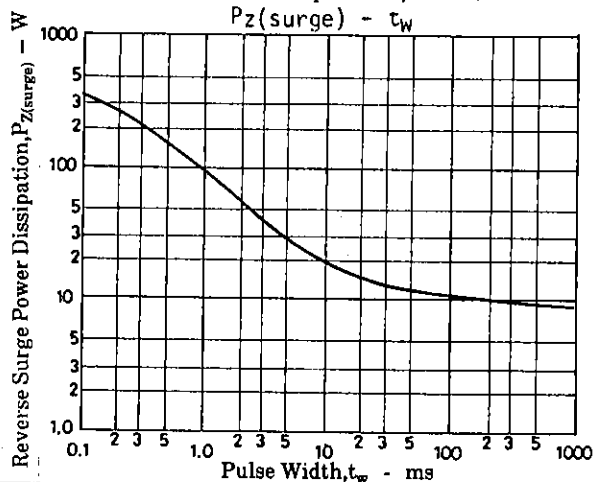
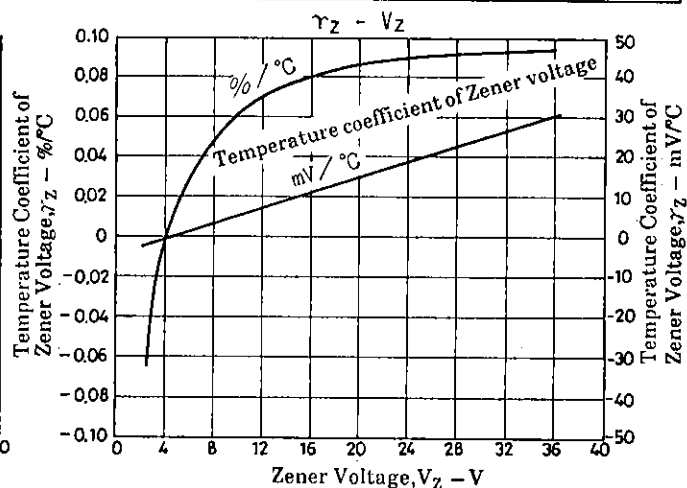
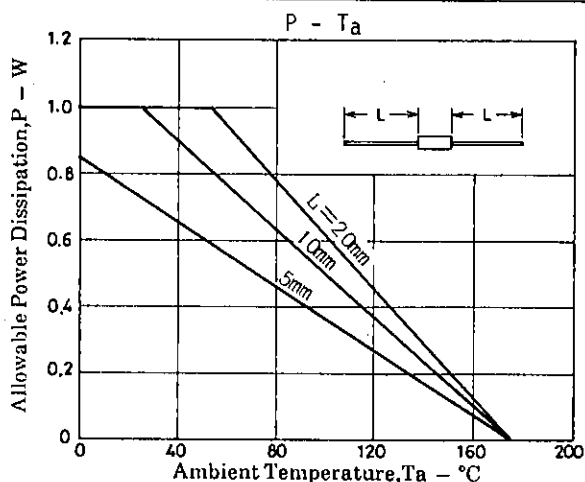
SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

GZB2.0 to 36

Continued from preceding page.

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Type No.	Zener Characteristics						Reverse Current		
	Zener Voltage, V_Z [V] ($t = 30\text{ms}$)				Dynamic Resistance r_d [Ω] $f = 1\text{kHz}$		Measured Current [mA]	I_R [μA]	Measured Voltage V_R [V]
	B		C		min	min			
	min	min	min	min					
GZB7.5	7.0	7.9	7.5	8.4	2	4	40	-20	-4
GZB8.2	7.7	8.7	8.2	9.3	2	4	40	-20	-5
GZB9.1	8.5	9.6	9.1	10.2	3	6	40	-20	-6
GZB10	9.4	10.6	10.0	11.2	3	6	40	-10	-7
GZB11	10.4	11.6	11.0	12.3	5	8	20	-10	-8
GZB12	11.4	12.6	12.0	13.5	5	8	20	-10	-9
GZB13	12.4	14.1	13.3	15.0	7	10	20	-10	-10
GZB15	13.8	15.6	14.7	16.5	7	10	20	-10	-11
GZB16	15.3	17.1	16.2	18.3	8	12	20	-10	-12
GZB18	16.8	19.1	18.0	20.3	8	12	20	-10	-13
GZB20	18.8	21.2	20.0	22.4	9	14	20	-10	-15
GZB22	20.8	23.3	22.0	24.5	9	14	10	-10	-17
GZB24	22.8	25.6	24.0	27.6	9	16	10	-10	-19
GZB27	25.1	28.9	27.0	30.8	9	16	10	-10	-21
GZB30	28.0	32.0	30.0	34.0	10	18	10	-10	-23
GZB33	31.0	35.0	33.0	37.0	10	18	10	-10	-25
GZB36	34.0	38.0	36.0	40.0	12	20	10	-10	-27



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